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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

### Applications of "[Embedded - Microcontrollers](#)"

#### Details

Product Status	Obsolete
Core Processor	dsPIC
Core Size	16-Bit
Speed	20 MIPS
Connectivity	CANbus, I <sup>2</sup> C, SPI, UART/USART
Peripherals	AC'97, Brown-out Detect/Reset, I <sup>2</sup> S, LVD, POR, PWM, WDT
Number of I/O	68
Program Memory Size	66KB (22K x 24)
Program Memory Type	FLASH
EEPROM Size	1K x 8
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	2.5V ~ 5.5V
Data Converters	A/D 16x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	80-TQFP
Supplier Device Package	80-TQFP (12x12)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/microchip-technology/dspic30f5013t-20i-pt">https://www.e-xfl.com/product-detail/microchip-technology/dspic30f5013t-20i-pt</a>

# dsPIC30F Flash Programming Specification

## 3.0 PROGRAMMING EXECUTIVE APPLICATION

### 3.1 Programming Executive Overview

The programming executive resides in executive memory and is executed when Enhanced ICSP Programming mode is entered. The programming executive provides the mechanism for the programmer (host device) to program and verify the dsPIC30F, using a simple command set and communication protocol.

The following capabilities are provided by the programming executive:

- Read memory
  - Code memory and data EEPROM
  - Configuration registers
  - Device ID
- Erase memory
  - Bulk Erase by segment
  - Code memory (by row)
  - Data EEPROM (by row)
- Program memory
  - Code memory
  - Data EEPROM
  - Configuration registers
- Query
  - Blank Device
  - Programming executive software version

The programming executive performs the low-level tasks required for erasing and programming. This allows the programmer to program the device by issuing the appropriate commands and data.

The programming procedure is outlined in [Section 5.0 “Device Programming”](#).

### 3.2 Programming Executive Code Memory

The programming executive is stored in executive code memory and executes from this reserved region of memory. It requires no resources from user code memory or data EEPROM.

### 3.3 Programming Executive Data RAM

The programming executive uses the device's data RAM for variable storage and program execution. Once the programming executive has run, no assumptions should be made about the contents of data RAM.

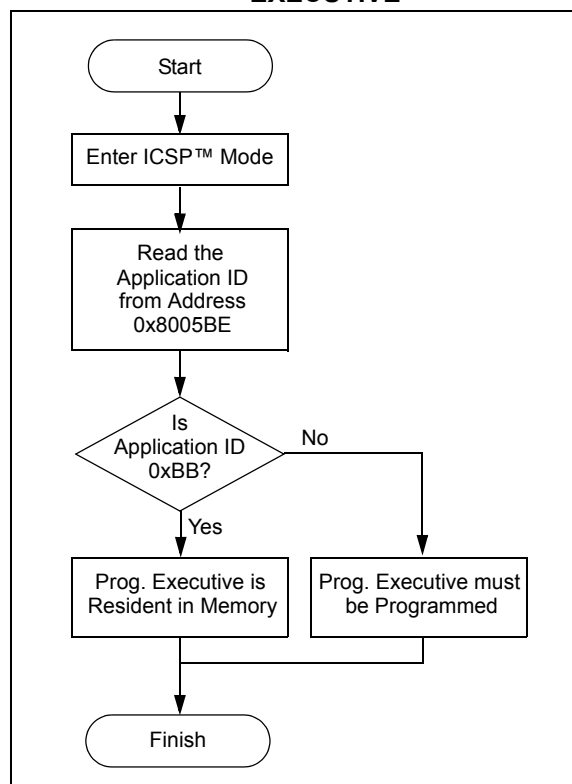
## 4.0 CONFIRMING THE CONTENTS OF EXECUTIVE MEMORY

Before programming can begin, the programmer must confirm that the programming executive is stored in executive memory. The procedure for this task is illustrated in [Figure 4-1](#).

First, ICSP mode is entered. The unique application ID word stored in executive memory is then read. If the programming executive is resident, the application ID word is 0xBB, which means programming can resume as normal. However, if the application ID word is not 0xBB, the programming executive must be programmed to Executive Code memory using the method described in [Section 12.0 “Programming the Programming Executive to Memory”](#).

[Section 11.0 “ICSP™ Mode”](#) describes the process for the ICSP programming method. [Section 11.13 “Reading the Application ID Word”](#) describes the procedure for reading the application ID word in ICSP mode.

**FIGURE 4-1: CONFIRMING PRESENCE OF THE PROGRAMMING EXECUTIVE**



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## 5.5 Code Memory Programming

### 5.5.1 OVERVIEW

The Flash code memory array consists of 512 rows of thirty-two, 24-bit instructions. Each panel stores 16K instruction words, and each dsPIC30F device has either 1, 2 or 3 memory panels (see Table 5-2).

**TABLE 5-2: DEVICE CODE MEMORY SIZE**

Device	Code Size (24-bit Words)	Number of Rows	Number of Panels
dsPIC30F2010	4K	128	1
dsPIC30F2011	4K	128	1
dsPIC30F2012	4K	128	1
dsPIC30F3010	8K	256	1
dsPIC30F3011	8K	256	1
dsPIC30F3012	8K	256	1
dsPIC30F3013	8K	256	1
dsPIC30F3014	8K	256	1
dsPIC30F4011	16K	512	1
dsPIC30F4012	16K	512	1
dsPIC30F4013	16K	512	1
dsPIC30F5011	22K	704	2
dsPIC30F5013	22K	704	2
dsPIC30F5015	22K	704	2
dsPIC30F5016	22K	704	2
dsPIC30F6010	48K	1536	3
dsPIC30F6010A	48K	1536	3
dsPIC30F6011	44K	1408	3
dsPIC30F6011A	44K	1408	3
dsPIC30F6012	48K	1536	3
dsPIC30F6012A	48K	1536	3
dsPIC30F6013	44K	1408	3
dsPIC30F6013A	44K	1408	3
dsPIC30F6014	48K	1536	3
dsPIC30F6014A	48K	1536	3
dsPIC30F6015	48K	1536	3

### 5.5.2 PROGRAMMING METHODOLOGY

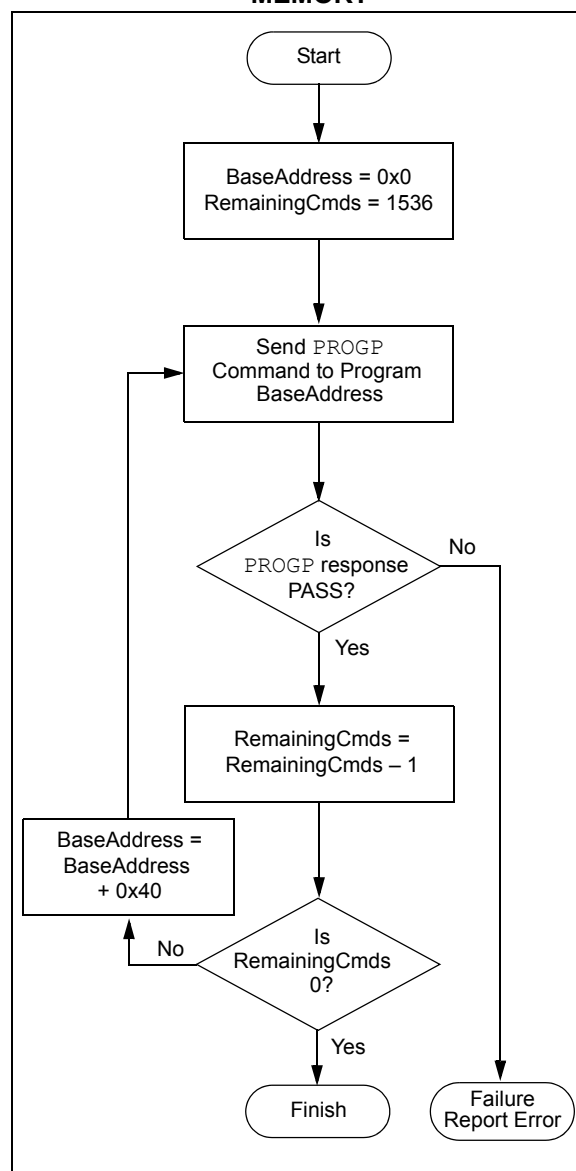
Code memory is programmed with the `PROGP` command. `PROGP` programs one row of code memory to the memory address specified in the command. The number of `PROGP` commands required to program a device depends on the number of rows that must be programmed in the device.

A flowchart for programming of code memory is illustrated in Figure 5-3. In this example, all 48K instruction words of a dsPIC30F6014A device are programmed. First, the number of commands to send (called 'RemainingCmds' in the flowchart) is set to 1536 and the destination address (called 'BaseAddress') is set to '0'.

Next, one row in the device is programmed with a `PROGP` command. Each `PROGP` command contains data for one row of code memory of the dsPIC30F6014A. After the first command is processed successfully, 'RemainingCmds' is decremented by 1 and compared to 0. Since there are more `PROGP` commands to send, 'BaseAddress' is incremented by 0x40 to point to the next row of memory.

On the second `PROGP` command, the second row of each memory panel is programmed. This process is repeated until the entire device is programmed. No special handling must be performed when a panel boundary is crossed.

**FIGURE 5-3: FLOWCHART FOR PROGRAMMING dsPIC30F6014A CODE MEMORY**



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**TABLE 5-6: FOSC CONFIGURATION BITS DESCRIPTION FOR dsPIC30F2011/2012, dsPIC30F3010/3011/3012/3013/3014, dsPIC30F4013, dsPIC30F5015/5016, dsPIC30F6010A/6011A/6012A/6013A/6014A AND dsPIC30F6015**

Bit Field	Register	Description
FCKSM<1:0>	FOSC	<b>Clock Switching Mode</b> 1x = Clock switching is disabled, Fail-Safe Clock Monitor is disabled 01 = Clock switching is enabled, Fail-Safe Clock Monitor is disabled 00 = Clock switching is enabled, Fail-Safe Clock Monitor is enabled
FOS<2:0>	FOSC	<b>Oscillator Source Selection on POR</b> 111 = Primary Oscillator 110 = Reserved 101 = Reserved 100 = Reserved 011 = Reserved 010 = Internal Low-Power RC Oscillator 001 = Internal Fast RC Oscillator (no PLL) 000 = Low-Power 32 kHz Oscillator (Timer1 Oscillator)
FPR<4:0>	FOSC	<b>Primary Oscillator Mode (when FOS&lt;2:0&gt; = 111b)</b> 11xxx = Reserved (do not use) 10111 = HS/3 w/PLL 16X – HS/3 crystal oscillator with 16X PLL (10 MHz-25 MHz crystal) 10110 = HS/3 w/PLL 8X – HS/3 crystal oscillator with 8X PLL (10 MHz-25 MHz crystal) 10101 = HS/3 w/PLL 4X – HS/3 crystal oscillator with 4X PLL (10 MHz-25 MHz crystal) 10100 = Reserved (do not use) 10011 = HS/2 w/PLL 16X – HS/2 crystal oscillator with 16X PLL (10 MHz-25 MHz crystal) 10010 = HS/2 w/PLL 8X – HS/2 crystal oscillator with 8X PLL (10 MHz-25 MHz crystal) 10001 = HS/2 w/PLL 4X – HS/2 crystal oscillator with 4X PLL (10 MHz-25 MHz crystal) 10000 = Reserved (do not use) 01111 = ECIO w/PLL 16x – External clock with 16x PLL. OSC2 pin is I/O 01110 = ECIO w/PLL 8x – External clock with 8x PLL. OSC2 pin is I/O 01101 = ECIO w/PLL 4x – External clock with 4x PLL. OSC2 pin is I/O 01100 = Reserved (do not use) 01011 = Reserved (do not use) 01010 = FRC w/PLL 8x – Internal fast RC oscillator with 8x PLL. OSC2 pin is I/O 01001 = Reserved (do not use) 01000 = Reserved (do not use) 00111 = XT w/PLL 16X – XT crystal oscillator with 16X PLL 00110 = XT w/PLL 8X – XT crystal oscillator with 8X PLL 00101 = XT w/PLL 4X – XT crystal oscillator with 4X PLL 00100 = Reserved (do not use) 00011 = FRC w/PLL 16x – Internal fast RC oscillator with 8x PLL. OSC2 pin is I/O 00010 = Reserved (do not use) 00001 = FRC w/PLL 4x – Internal fast RC oscillator with 4x PLL. OSC2 pin is I/O 00000 = Reserved (do not use)

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**TABLE 5-6: FOSC CONFIGURATION BITS DESCRIPTION FOR dsPIC30F2011/2012, dsPIC30F3010/3011/3012/3013/3014, dsPIC30F4013, dsPIC30F5015/5016, dsPIC30F6010A/6011A/6012A/6013A/6014A AND dsPIC30F6015 (CONTINUED)**

Bit Field	Register	Description
FPR<4:0>	FOSC	<b>Alternate Oscillator Mode (when FOS&lt;2:0&gt; = 011b)</b> 1xxxx = Reserved (do not use) 0111x = Reserved (do not use) 01101 = Reserved (do not use) 01100 = ECIO – External clock. OSC2 pin is I/O 01011 = EC – External clock. OSC2 pin is system clock output (Fosc/4) 01010 = Reserved (do not use) 01001 = ERC – External RC oscillator. OSC2 pin is system clock output (Fosc/4) 01000 = ERCIO – External RC oscillator. OSC2 pin is I/O 00111 = Reserved (do not use) 00110 = Reserved (do not use) 00101 = Reserved (do not use) 00100 = XT – XT crystal oscillator (4 MHz-10 MHz crystal) 00010 = HS – HS crystal oscillator (10 MHz-25 MHz crystal) 00001 = Reserved (do not use) 00000 = XTL – XTL crystal oscillator (200 kHz-4 MHz crystal)

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**TABLE 5-7: CONFIGURATION BITS DESCRIPTION**

Bit Field	Register	Description
FWPSA<1:0>	FWDT	<b>Watchdog Timer Prescaler A</b> 11 = 1:512 10 = 1:64 01 = 1:8 00 = 1:1
FWPSB<3:0>	FWDT	<b>Watchdog Timer Prescaler B</b> 1111 = 1:16 1110 = 1:15 . . . 0001 = 1:2 0000 = 1:1
FWDTEN	FWDT	<b>Watchdog Enable</b> 1 = Watchdog enabled (LPRC oscillator cannot be disabled. Clearing the SWDTEN bit in the RCON register will have no effect) 0 = Watchdog disabled (LPRC oscillator can be disabled by clearing the SWDTEN bit in the RCON register)
MCLREN	FBORPOR	<b>Master Clear Enable</b> 1 = Master Clear pin (MCLR) is enabled 0 = MCLR pin is disabled
PWMPIN	FBORPOR	<b>Motor Control PWM Module Pin Mode</b> 1 = PWM module pins controlled by PORT register at device Reset (tri-stated) 0 = PWM module pins controlled by PWM module at device Reset (configured as output pins)
HPOL	FBORPOR	<b>Motor Control PWM Module High-Side Polarity</b> 1 = PWM module high-side output pins have active-high output polarity 0 = PWM module high-side output pins have active-low output polarity
LPOL	FBORPOR	<b>Motor Control PWM Module Low-Side Polarity</b> 1 = PWM module low-side output pins have active-high output polarity 0 = PWM module low-side output pins have active-low output polarity
BOREN	FBORPOR	<b>PBOR Enable</b> 1 = PBOR enabled 0 = PBOR disabled
BORV<1:0>	FBORPOR	<b>Brown-out Voltage Select</b> 11 = 2.0V (not a valid operating selection) 10 = 2.7V 01 = 4.2V 00 = 4.5V
FPWRT<1:0>	FBORPOR	<b>Power-on Reset Timer Value Select</b> 11 = PWRT = 64 ms 10 = PWRT = 16 ms 01 = PWRT = 4 ms 00 = Power-up Timer disabled
RBS<1:0>	FBS	<b>Boot Segment Data RAM Code Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015)</b> 11 = No Data RAM is reserved for Boot Segment 10 = Small-sized Boot RAM [128 bytes of RAM are reserved for Boot Segment] 01 = Medium-sized Boot RAM [256 bytes of RAM are reserved for Boot Segment] 00 = Large-sized Boot RAM [512 bytes of RAM are reserved for Boot Segment in dsPIC30F5011/5013, and 1024 bytes in dsPIC30F6010A/6011A/6012A/6013A/6014A/6015]

# dsPIC30F Flash Programming Specification

**TABLE 5-7: CONFIGURATION BITS DESCRIPTION (CONTINUED)**

Bit Field	Register	Description
SSS<2:0>	FSS	<b>Secure Segment Program Memory Code Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015)</b> 111 = No Secure Segment 110 = Standard security; Small-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x001FFF] 101 = Standard security; Medium-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x003FFF] 100 = Standard security; Large-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x007FFF] 011 = No Secure Segment 010 = High security; Small-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x001FFF] 001 = High security; Medium-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x003FFF] 000 = High security; Large-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x007FFF]
SWRP	FSS	<b>Secure Segment Program Memory Write Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015)</b> 1 = Secure Segment program memory is not write-protected 0 = Secure program memory is write-protected
GSS<1:0>	FGS	<b>General Segment Program Memory Code Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015)</b> 11 = Code protection is disabled 10 = Standard security code protection is enabled 0x = High security code protection is enabled
GCP	FGS	<b>General Segment Program Memory Code Protection (present in all devices except dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015)</b> 1 = General Segment program memory is not code-protected 0 = General Segment program memory is code-protected
GWRP	FGS	<b>General Segment Program Memory Write Protection</b> 1 = General Segment program memory is not write-protected 0 = General Segment program memory is write-protected
BKBUG	FICD	<b>Debugger/Emulator Enable</b> 1 = Device will reset into Operational mode 0 = Device will reset into Debug/Emulation mode
COE	FICD	<b>Debugger/Emulator Enable</b> 1 = Device will reset into Operational mode 0 = Device will reset into Clip-on Emulation mode
ICS<1:0>	FICD	<b>ICD Communication Channel Select</b> 11 = Communicate on PGC/EMUC and PGD/EMUD 10 = Communicate on EMUC1 and EMUD1 01 = Communicate on EMUC2 and EMUD2 00 = Communicate on EMUC3 and EMUD3
RESERVED	FBS, FSS, FGS	<b>Reserved (read as '1', write as '1')</b>
—	All	<b>Unimplemented (read as '0', write as '0')</b>

**TABLE 5-8: dsPIC30F CONFIGURATION REGISTERS (FOR dsPIC30F2010, dsPIC30F4011/4012 AND dsPIC30F6010/ 6011/6012/6013/ 6014)**

Address	Name	Bit 15	Bit 14	Bit 13	Bit 12	Bit 11	Bit 10	Bit 9	Bit 8	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
0xF80000	FOSC	FCKSM<1:0>		—	—	—	—	FOS<1:0>		—	—	—	—	FPR<3:0>			
0xF80002	FWDT	FWDTEN	—	—	—	—	—	—	—	—	—	FWPSA<1:0>		FWPSB<3:0>			
0xF80004	FBORPOR	MCLREN	—	—	—	—	PWMPIN <sup>(1)</sup>	HPOL <sup>(1)</sup>	LPOL <sup>(1)</sup>	BOREN	—	BORV<1:0>		—	—	FPWRT<1:0>	
0xF80006	FBS	—	—	Reserved <sup>(2)</sup>		—	—	—	Reserved <sup>(2)</sup>	—	—	—	—	Reserved <sup>(2)</sup>			
0xF80008	FSS	—	—	Reserved <sup>(2)</sup>		—	—	Reserved <sup>(2)</sup>		—	—	—	—	Reserved <sup>(2)</sup>			
0xF8000A	FGS	—	—	—	—	—	—	—	—	—	—	—	—	—	Reserved <sup>(2)</sup>	GCP	GWRP
0xF8000C	FICD	BKBUG	COE	—	—	—	—	—	—	—	—	—	—	—	—	ICS<1:0>	

**Note 1:** On the 6011, 6012, 6013 and 6014, these bits are reserved (read as '1' and must be programmed as '1').

**Note 2:** Reserved bits read as '1' and must be programmed as '1'.

**TABLE 5-9: dsPIC30F CONFIGURATION REGISTERS (FOR dsPIC30F5011/5013)**

Address	Name	Bit 15	Bit 14	Bit 13	Bit 12	Bit 11	Bit 10	Bit 9	Bit 8	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
0xF80000	FOSC	FCKSM<1:0>		—	—	—	—	FOS<1:0>		—	—	—	—	FPR<3:0>			
0xF80002	FWDT	FWDTEN	—	—	—	—	—	—	—	—	—	FWPSA<1:0>		FWPSB<3:0>			
0xF80004	FBORPOR	MCLREN	—	—	—	—	Reserved <sup>(1)</sup>			BOREN	—	BORV<1:0>		—	—	FPWRT<1:0>	
0xF80006	FBS	—	—	RBS<1:0>		—	—	—	EBS	—	—	—	—	BSS<2:0>			BWRP
0xF80008	FSS	—	—	RSS<1:0>		—	—	ESS<1:0>		—	—	—	—	SSS<2:0>			SWRP
0xF8000A	FGS	—	—	—	—	—	—	—	—	—	—	—	—	—	GSS<1:0>		GWRP
0xF8000C	FICD	BKBUG	COE	—	—	—	—	—	—	—	—	—	—	—	—	ICS<1:0>	

**Note 1:** Reserved bits read as '1' and must be programmed as '1'.



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TABLE 8-1: PROGRAMMING EXECUTIVE COMMAND SET

Opcode	Mnemonic	Length (16-bit words)	Time Out	Description
0x0	SCHECK	1	1 ms	Sanity check.
0x1	READD	4	1 ms/row	Read N 16-bit words of data EEPROM, Configuration registers or device ID starting from specified address.
0x2	READP	4	1 ms/row	Read N 24-bit instruction words of code memory starting from specified address.
0x3	Reserved	N/A	N/A	This command is reserved. It will return a NACK.
0x4	PROGD <sup>(2)</sup>	19	5 ms	Program one row of data EEPROM at the specified address, then verify.
0x5	PROGP <sup>(1)</sup>	51	5 ms	Program one row of code memory at the specified address, then verify.
0x6	PROGC	4	5 ms	Write byte or 16-bit word to specified Configuration register.
0x7	ERASEB	2	5 ms	Bulk Erase (entire code memory or data EEPROM), or erase by segment.
0x8	ERASED <sup>(2)</sup>	3	5 ms/row	Erase rows of data EEPROM from specified address.
0x9	ERASEP <sup>(1)</sup>	3	5 ms/row	Erase rows of code memory from specified address.
0xA	QBLANK	3	300 ms	Query if the code memory and data EEPROM are blank.
0xB	QVER	1	1 ms	Query the programming executive software version.

**Note 1:** One row of code memory consists of (32) 24-bit words. Refer to [Table 5-2](#) for device-specific information.

**Note 2:** One row of data EEPROM consists of (16) 16-bit words. Refer to [Table 5-3](#) for device-specific information.

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## 8.5.5 PROGP COMMAND

15	12	11	8	7	0
Opcode		Length			
Reserved			Addr_MSB		
Addr_LS					
D_1					
D_2					
...					
D_N					

Field	Description
Opcode	0x5
Length	0x33
Reserved	0x0
Addr_MSB	MSB of 24-bit destination address
Addr_LS	LS 16 bits of 24-bit destination address
D_1	16-bit data word 1
D_2	16-bit data word 2
...	16-bit data word 3 through 47
D_48	16-bit data word 48

The **PROGP** command instructs the programming executive to program one row of code memory (32 instruction words) to the specified memory address. Programming begins with the row address specified in the command. The destination address should be a multiple of 0x40.

The data to program to memory, located in command words D\_1 through D\_48, must be arranged using the packed instruction word format shown in [Figure 8-2](#).

After all data has been programmed to code memory, the programming executive verifies the programmed data against the data in the command.

### Expected Response (2 words):

0x1500  
0x0002

**Note:** Refer to [Table 5-2](#) for code memory size information.

## 8.5.6 PROGC COMMAND

15	12	11	8	7	0
Opcode		Length			
Reserved			Addr_MSB		
Addr_LS					
Data					

Field	Description
Opcode	0x6
Length	0x4
Reserved	0x0
Addr_MSB	MSB of 24-bit destination address
Addr_LS	LS 16 bits of 24-bit destination address
Data	Data to program

The **PROGC** command programs data to the specified Configuration register and verifies the programming. Configuration registers are 16 bits wide, and this command allows one Configuration register to be programmed.

### Expected Response (2 words):

0x1600  
0x0002

**Note:** This command can only be used for programming Configuration registers.

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## 8.5.9 ERASEP COMMAND

15	12	11	8	7	0
Opcode		Length			
Num_Rows			Addr_MSB		
Addr_LS					

Field	Description
Opcode	0x9
Length	0x3
Num_Rows	Number of rows to erase
Addr_MSB	MSB of 24-bit base address
Addr_LS	LS 16 bits of 24-bit base address

The **ERASEP** command erases the specified number of rows of code memory from the specified base address. The specified base address must be a multiple of 0x40.

Once the erase is performed, all targeted words of code memory contain 0xFFFFFFFF.

### Expected Response (2 words):

0x1900  
0x0002

**Note:** The **ERASEP** command cannot be used to erase the Configuration registers or device ID. Code-protect Configuration registers can only be erased with the **ERASEB** command, while the device ID is read-only.

## 8.5.10 QBLANK COMMAND

15	12	11	0
Opcode	Length		
PSize			
Reserved	DSize		

Field	Description
Opcode	0xA
Length	0x3
PSize	Length of program memory to check (in 24-bit words), max of 49152
Reserved	0x0
DSize	Length of data memory to check (in 16-bit words), max of 2048

The **QBLANK** command queries the programming executive to determine if the contents of code memory and data EEPROM are blank (contains all '1's). The size of code memory and data EEPROM to check must be specified in the command.

The Blank Check for code memory begins at 0x0 and advances toward larger addresses for the specified number of instruction words. The Blank Check for data EEPROM begins at 0x7FFFFE and advances toward smaller addresses for the specified number of data words.

**QBLANK** returns a **QE\_Code** of 0xF0 if the specified code memory and data EEPROM are blank. Otherwise, **QBLANK** returns a **QE\_Code** of 0x0F.

### Expected Response (2 words for blank device):

0x1AF0  
0x0002

### Expected Response (2 words for non-blank device):

0x1A0F  
0x0002

**Note:** The **QBLANK** command does not check the system Configuration registers. The **READD** command must be used to determine the state of the Configuration registers.

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## 8.5.11 QVER COMMAND

15	12	11	0
Opcode	Length		

Field	Description
Opcode	0xB
Length	0x1

The QVER command queries the version of the programming executive software stored in test memory. The “version.revision” information is returned in the response’s QE\_Code using a single byte with the following format: main version in upper nibble and revision in the lower nibble (i.e., 0x23 is version 2.3 of programming executive software).

### Expected Response (2 words):

0x1BMN (where “MN” stands for version M.N)  
0x0002

## 9.0 PROGRAMMING EXECUTIVE RESPONSES

### 9.1 Overview

The programming executive sends a response to the programmer for each command that it receives. The response indicates if the command was processed correctly, and includes any required response or error data.

The programming executive response set is shown in Table 9-1. This table contains the opcode, mnemonic and description for each response. The response format is described in Section 9.2 “Response Format”.

**TABLE 9-1: PROGRAMMING EXECUTIVE RESPONSE SET**

Opcode	Mnemonic	Description
0x1	PASS	Command successfully processed.
0x2	FAIL	Command unsuccessfully processed.
0x3	NACK	Command not known.

## 9.2 Response Format

As shown in Example 9-1, all programming executive responses have a general format consisting of a two word header and any required data for the command. Table 9-2 lists the fields and their descriptions.

**EXAMPLE 9-1: FORMAT**

15	12	11	8	7	0
Opcode	Last_Cmd		QE_Code		
Length					
D_1 (if applicable)					
...					
D_N (if applicable)					

**TABLE 9-2: FIELDS AND DESCRIPTIONS**

Field	Description
Opcode	Response opcode.
Last_Cmd	Programmer command that generated the response.
QE_Code	Query code or Error code.
Length	Response length in 16-bit words (includes 2 header words.)
D_1	First 16-bit data word (if applicable).
D_N	Last 16-bit data word (if applicable).

### 9.2.1 Opcode FIELD

The Opcode is a 4-bit field in the first word of the response. The Opcode indicates how the command was processed (see Table 9-1). If the command is processed successfully, the response opcode is PASS. If there is an error in processing the command, the response opcode is FAIL, and the QE\_Code indicates the reason for the failure. If the command sent to the programming executive is not identified, the programming executive returns a NACK response.

### 9.2.2 Last\_Cmd FIELD

The Last\_Cmd is a 4-bit field in the first word of the response and indicates the command that the programming executive processed. Since the programming executive can only process one command at a time, this field is technically not required. However, it can be used to verify whether the programming executive correctly received the command that the programmer transmitted.

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## 11.0 ICSP™ MODE

### 11.1 ICSP Mode

ICSP mode is a special programming protocol that allows you to read and write to the dsPIC30F programming executive. The ICSP mode is the second (and slower) method used to program the device. This mode also has the ability to read the contents of executive memory to determine whether the programming executive is present. This capability is accomplished by applying control codes and instructions serially to the device using pins PGC and PGD.

In ICSP mode, the system clock is taken from the PGC pin, regardless of the device's oscillator Configuration bits. All instructions are first shifted serially into an internal buffer, then loaded into the Instruction register and executed. No program fetching occurs from internal memory. Instructions are fed in 24 bits at a time. PGD is used to shift data in and PGC is used as both the serial shift clock and the CPU execution clock.

Data is transmitted on the rising edge and latched on the falling edge of PGC. For all data transmissions, the Least Significant bit (LSb) is transmitted first.

**Note 1:** During ICSP operation, the operating frequency of PGC must not exceed 5 MHz.

**2:** Because ICSP is slower, it is recommended that only Enhanced ICSP (E-ICSP) mode be used for device programming, as described in [Section 5.1 "Overview of the Programming Process"](#).

### 11.2 ICSP Operation

Upon entry into ICSP mode, the CPU is idle. Execution of the CPU is governed by an internal state machine. A 4-bit control code is clocked in using PGC and PGD, and this control code is used to command the CPU (see [Table 11-1](#)).

The SIX control code is used to send instructions to the CPU for execution, while the REGOUT control code is used to read data out of the device via the VISI register. The operation details of ICSP mode are provided in [Section 11.2.1 "SIX Serial Instruction Execution"](#) and [Section 11.2.2 "REGOUT Serial Instruction Execution"](#).

**TABLE 11-1: CPU CONTROL CODES IN ICSP™ MODE**

4-bit Control Code	Mnemonic	Description
0000b	SIX	Shift in 24-bit instruction and execute.
0001b	REGOUT	Shift out the VISI register.
0010b-1111b	N/A	Reserved.

#### 11.2.1 SIX SERIAL INSTRUCTION EXECUTION

The SIX control code allows execution of dsPIC30F assembly instructions. When the SIX code is received, the CPU is suspended for 24 clock cycles as the instruction is then clocked into the internal buffer. Once the instruction is shifted in, the state machine allows it to be executed over the next four clock cycles. While the received instruction is executed, the state machine simultaneously shifts in the next 4-bit command (see [Figure 11-2](#)).

**Note 1:** Coming out of the ICSP entry sequence, the first 4-bit control code is always forced to SIX and a forced NOP instruction is executed by the CPU. Five additional PGC clocks are needed on start-up, thereby resulting in a 9-bit SIX command instead of the normal 4-bit SIX command. After the forced SIX is clocked in, ICSP operation resumes as normal (the next 24 clock cycles load the first instruction word to the CPU). See [Figure 11-1](#) for details.

**2:** TBLRDH, TBLRDL, TBLWTH and TBLWTL instructions must be followed by a NOP instruction.

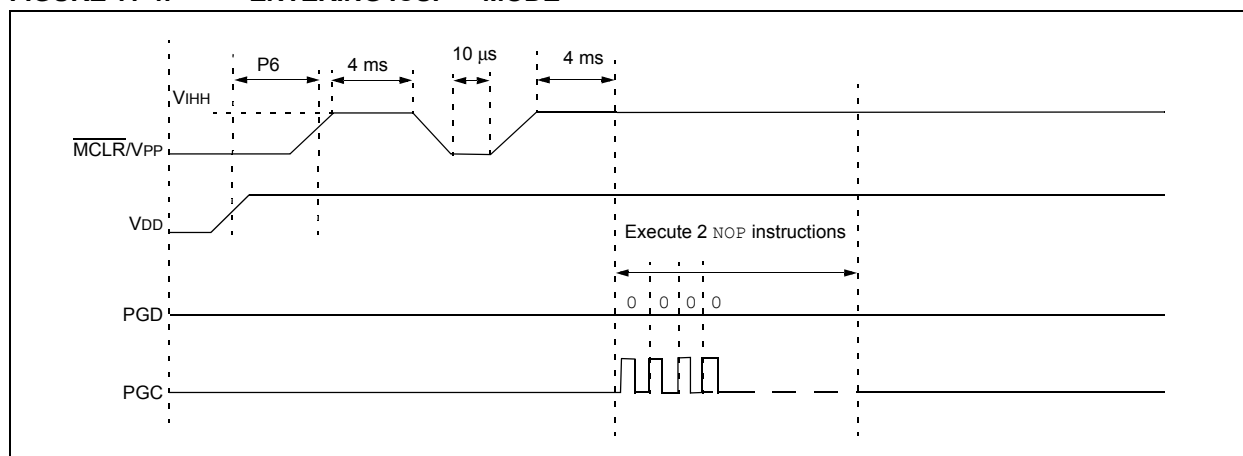
# dsPIC30F Flash Programming Specification

## 11.3 Entering ICSP Mode

The ICSP mode is entered by holding PGC and PGD low, raising MCLR/VPP to VIH (high voltage), and then performing additional steps as illustrated in [Figure 11-4](#).

- Note 1:** The sequence that places the device into ICSP mode places all unused I/O pins to the high-impedance state.
- 2:** Once ICSP mode is entered, the PC is set to 0x0 (the Reset vector).
- 3:** Before leaving the Reset vector, execute two GOTO instructions, followed by a single NOP instruction must be executed.

**FIGURE 11-4: ENTERING ICSP™ MODE**



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**TABLE 11-5: SERIAL INSTRUCTION EXECUTION FOR ERASING PROGRAM MEMORY  
(EITHER IN LOW-VOLTAGE OR NORMAL-VOLTAGE SYSTEMS) (CONTINUED)**

Command (Binary)	Data (Hexadecimal)	Description
<b>Step 6:</b> Update the row address stored in NVMADRU:NVMADR. When W6 rolls over to 0x0, NVMADRU must be incremented.		
0000	430307	ADD W6, W7, W6
0000	AF0042	BTSC SR, #C
0000	EC2764	INC NVMADRU
0000	883B16	MOV W6, NVMADR
<b>Step 7:</b> Reset device internal PC.		
0000	040100	GOTO 0x100
0000	000000	NOP
<b>Step 8:</b> Repeat Steps 3-7 until all rows of code memory are erased.		
<b>Step 9:</b> Initialize NVMADR and NVMADRU to erase executive memory and initialize W7 for row address updates.		
0000	EB0300	CLR W6
0000	883B16	MOV W6, NVMADR
0000	200807	MOV #0x80, W7
0000	883B27	MOV W7, NVMADRU
0000	200407	MOV #0x40, W7
<b>Step 10:</b> Set NVMCON to erase 1 row of executive memory.		
0000	24071A	MOV #0x4071, W10
0000	883B0A	MOV W10, NVMCON
<b>Step 11:</b> Unlock the NVMCON to erase 1 row of executive memory.		
0000	200558	MOV #0x55, W8
0000	883B38	MOV W8, NVMKEY
0000	200AA9	MOV #0xAA, W9
0000	883B39	MOV W9, NVMKEY
<b>Step 12:</b> Initiate the erase cycle.		
0000	A8E761	BSET NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
—	—	Externally time 'P13a' ms (see <a href="#">Section 13.0 “AC/DC Characteristics and Timing Requirements”</a> )
0000	000000	NOP
0000	000000	NOP
0000	A9E761	BCLR NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
<b>Step 13:</b> Update the row address stored in NVMADR.		
0000	430307	ADD W6, W7, W6
0000	883B16	MOV W6, NVMADR
<b>Step 14:</b> Reset device internal PC.		
0000	040100	GOTO 0x100
0000	000000	NOP
<b>Step 15:</b> Repeat Steps 10-14 until all 24 rows of executive memory are erased.		
<b>Step 16:</b> Initialize NVMADR and NVMADRU to erase data memory and initialize W7 for row address updates.		
0000	2XXXX6	MOV #<lower 16-bits of starting Data EEPROM address>, W6
0000	883B16	MOV W6, NVMADR
0000	2007F6	MOV #0x7F, W6
0000	883B16	MOV W6, NVMADRU
0000	200207	MOV #0x20, W7
<b>Step 17:</b> Set NVMCON to erase 1 row of data memory.		
0000	24075A	MOV #0x4075, W10
0000	883B0A	MOV W10, NVMCON

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**TABLE 11-8: SERIAL INSTRUCTION EXECUTION FOR WRITING CODE MEMORY (CONTINUED)**

Command (Binary)	Data (Hexadecimal)	Description
<b>Step 5:</b> Set the read pointer (W6) and load the (next set of) write latches.		
0000	EB0300	CLR W6
0000	000000	NOP
0000	BB0BB6	TBLWTL [W6++], [W7]
0000	000000	NOP
0000	000000	NOP
0000	BBDDB6	TBLWTH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BBE6B6	TBLWTH.B [W6++], [++W7]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BB0BB6	TBLWTL [W6++], [W7]
0000	000000	NOP
0000	000000	NOP
0000	BBDDB6	TBLWTH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BBE6B6	TBLWTH.B [W6++], [++W7]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
<b>Step 6:</b> Repeat steps 4-5 eight times to load the write latches for 32 instructions.		
<b>Step 7:</b> Unlock the NVMCON for writing.		
0000	200558	MOV #0x55, W8
0000	883B38	MOV W8, NVMKEY
0000	200AA9	MOV #0xAA, W9
0000	883B39	MOV W9, NVMKEY
<b>Step 8:</b> Initiate the write cycle.		
0000	A8E761	BSET NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
—	—	Externally time 'P12a' ms (see <a href="#">Section 13.0 “AC/DC Characteristics and Timing Requirements”</a> )
0000	000000	NOP
0000	000000	NOP
0000	A9E761	BCLR NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
<b>Step 9:</b> Reset device internal PC.		
0000	040100	GOTO 0x100
0000	000000	NOP
<b>Step 10:</b> Repeat steps 2-9 until all code memory is programmed.		



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## 11.9 Writing Data EEPROM

The procedure for writing data EEPROM is very similar to the procedure for writing code memory, except that fewer words are programmed in each operation. When writing data EEPROM, one row of data EEPROM is programmed at a time. Each row consists of sixteen 16-bit data words. Since fewer words are programmed

during each operation, only working registers W0:W3 are used as temporary holding registers for the data to be programmed.

Table 11-9 shows the ICSP programming details for writing data EEPROM. Note that a different NVMCON value is required to write to data EEPROM, and that the TBLPAG register is hard-coded to 0x7F (the upper byte address of all locations of data EEPROM).

**TABLE 11-9: SERIAL INSTRUCTION EXECUTION FOR WRITING DATA EEPROM**

Command (Binary)	Data (Hexadecimal)	Description
<b>Step 1: Exit the Reset vector.</b>		
0000	040100	GOTO 0x100
0000	040100	GOTO 0x100
0000	000000	NOP
<b>Step 2: Set the NVMCON to write 16 data words.</b>		
0000	24005A	MOV #0x4005, W10
0000	883B0A	MOV W10, NVMCON
<b>Step 3: Initialize the write pointer (W7) for TBLWT instruction.</b>		
0000	2007F0	MOV #0x7F, W0
0000	880190	MOV W0, TBLPAG
0000	2xxxx7	MOV #<DestinationAddress15:0>, W7
<b>Step 4: Load W0:W3 with the next 4 data words to program.</b>		
0000	2xxxx0	MOV #<WORD0>, W0
0000	2xxxx1	MOV #<WORD1>, W1
0000	2xxxx2	MOV #<WORD2>, W2
0000	2xxxx3	MOV #<WORD3>, W3
<b>Step 5: Set the read pointer (W6) and load the (next set of) write latches.</b>		
0000	EB0300	CLR W6
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
<b>Step 6: Repeat steps 4-5 four times to load the write latches for 16 data words.</b>		

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**TABLE 11-10: SERIAL INSTRUCTION EXECUTION FOR READING CODE MEMORY (CONTINUED)**

Command (Binary)	Data (Hexadecimal)	Description
<b>Step 4: Output W0:W5 using the VISI register and REGOUT command.</b>		
0000	883C20	MOV W0, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
0000	883C21	MOV W1, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
0000	883C22	MOV W2, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
0000	883C23	MOV W3, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
0000	883C24	MOV W4, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
0000	883C25	MOV W5, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
<b>Step 5: Reset the device internal PC.</b>		
0000	040100	GOTO 0x100
0000	000000	NOP
<b>Step 6: Repeat steps 3-5 until all desired code memory is read.</b>		

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**TABLE 13-1: AC/DC CHARACTERISTICS (CONTINUED)**

AC/DC CHARACTERISTICS			Standard Operating Conditions (unless otherwise stated) Operating Temperature: 25° C is recommended			
Param. No.	Sym	Characteristic	Min	Max	Units	Conditions
P9b	TDLY5	Delay between PGD ↓ by programming executive to PGD released by programming executive	15	—	μs	—
P10	TDLY6	Delay between PGD released by programming executive to first PGC ↑ of response	5	—	μs	—
P11	TDLY7	Delay between clocking out response words	10	—	μs	—
P12a	TPROG	Row Programming cycle time	1	4	ms	ICSP mode
P12b	TPROG	Row Programming cycle time	0.8	2.6	ms	Enhanced ICSP mode
P13a	TERA	Bulk/Row Erase cycle time	1	4	ms	ICSP mode
P13b	TERA	Bulk/Row Erase cycle time	0.8	2.6	ms	Enhanced ICSP mode

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**TABLE A-1: CHECKSUM COMPUTATION (CONTINUED)**

Device	Read Code Protection	Checksum Computation	Erased Value	Value with 0xAAAAAA at 0x0 and Last Code Address
dsPIC30F5016	Disabled	CFGB+SUM(0:00AFFF)	0xFC06	0xFA08
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6010	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6010A	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6011	Disabled	CFGB+SUM(0:015FFF)	0xF406	0xF208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6011A	Disabled	CFGB+SUM(0:015FFF)	0xF406	0xF208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6012	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6012A	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6013	Disabled	CFGB+SUM(0:015FFF)	0xF406	0xF208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6013A	Disabled	CFGB+SUM(0:015FFF)	0xF406	0xF208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6014	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6014A	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6015	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404

**Item Description:**

**SUM(a:b)** = Byte sum of locations a to b inclusive (all 3 bytes of code memory)

**CFGB** = **Configuration Block (masked)** = Byte sum of ((FOSC&0xC10F) + (FWDT&0x803F) + (FBORPOR&0x87B3) + (FBS&0x310F) + (FSS&0x330F) + (FGS&0x0007) + (FICD&0xC003))

## APPENDIX C: REVISION HISTORY

<b>Note:</b> Revision histories were not recorded for revisions A through H. The previous revision (J), was published in August 2007.
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### Revision K (November 2010)

This version of the document includes the following updates:

- Added Note three to [Section 5.2 “Entering Enhanced ICSP Mode”](#)
- Updated the first paragraph of [Section 10.0 “Device ID”](#)
- Updated [Table 10-1: Device IDs](#)
- Removed the VARIANT bit and updated the bit definition for the DEVID register in [Table 10-2: dsPIC30F Device ID Registers](#)
- Removed the VARIANT bit and updated the bit field definition and description for the DEVID register in [Table 10-3: Device ID Bits Description](#)
- Updated Note 3 in [Section 11.3 “Entering ICSP Mode”](#)
- Updated Step 11 in [Table 11-4: Serial Instruction Execution for Bulk Erasing Program Memory \(Only in Normal-voltage Systems\)](#)
- Updated Steps 5, 12 and 19 in [Table 11-5: Serial Instruction Execution for Erasing Program Memory \(Either in Low-voltage or Normal-voltage Systems\)](#)
- Updated Steps 5, 6 and 8 in [Table 11-7: Serial Instruction Execution for Writing Configuration Registers](#)
- Updated Steps 6 and 8 in [Table 11-8: Serial Instruction Execution for Writing Code Memory](#)
- Updated Steps 6 and 8 in [Table 11-9: Serial Instruction Execution for Writing Data EEPROM](#)
- Updated Entering ICSP™ Mode (see [Figure 11-4](#))
- Updated Steps 4 and 11 in [Table 12-1: Programming the Programming Executive](#)
- Renamed parameters: P12 to P12a and P13 to P13a, and added parameters P12b and P13b in [Table 13-1: AC/DC Characteristics](#)